



13/D
W/ATTACH
MENT. 6/20/02
Mullish

Docket No.: M4065.0139/P139-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Cem Basceri

Application No.: 09/633,132

Group Art Unit: 2815

Filed: August 4, 2000

Examiner: E. Lee

For: METHOD FOR IMPROVING THE
SIDEWALL STOICHIOMETRY OF THIN
FILM CAPACITORS

RECEIVED
JUN 13 2002
TECHNOLOGY CENTER 2800

AMENDMENT

Box Non Final Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated March 12, 2002, rejecting claims 39, 41-48, 50-56 and 74-83, please amend the application as follows and reconsider the above-identified U.S. patent application in light of the following remarks:

In the Claims

39. (Third Amended) A capacitor comprising:

DI
a material layer having a first level and a second level, said first and second levels being connected by a sidewall region between said first and second levels; and

sub 7
EI
a post deposition doped BST high dielectric constant thin film material formed on at least one said sidewall region, wherein the stoichiometry of said BST high dielectric thin film material is substantially uniform at least at said sidewall region.